

## IN THE SPECIFICATION

Please replace the Abstract of the Disclosure with the following rewritten Abstract:

~~Embodiments of the invention provide a flash memory device having a column predecoder for selecting all column selection transistors during a stress test, and also provide a stress test method for the flash memory device. An embodiment's~~ A column predecoder includes a buffer unit for inputting all column selection signals, decoder units for decoding an output of the buffer unit and column addresses, and level shifters for shifting voltage levels of column selection signals coupled to gates of the column selection transistors in response to an output of the decoder units. Since a ground voltage is applied to a bitline and a high voltage is applied to all column selection signals during the stress test, the stress test time can be shortened.